SP8M2

Transistors

4V Drive Nch+Pch MOSFET SP8M2

Structure

Silicon N-channel MOSFET / Silicon P-channel MOSFET

Features

- 1) Low on-resistance.
- 2) Built-in G-S protection diode.
- 3) Small surface mount package (SOP8).

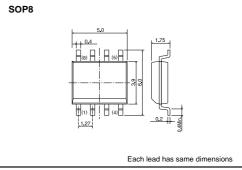
Applications

Switching

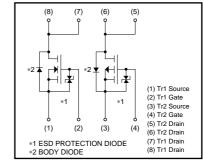
Package specifications

	Package	Taping
Туре	Code	ТВ
	Basic ordering unit (pieces)	2500
SP8M2		0

•Dimensions (Unit : mm)



Inner circuit



Absolute maximum ratings (Ta=25°C)

Parameter		Symbol	Lin	Unit					
		Symbol	Tr1 : N-ch	Tr2 : P-ch	Onit				
Drain-source voltage		V _{DSS}	30	-30	V				
Gate-source voltage		Vgss	±20	±20	V				
Drain current	Continuous	ID	±3.5	±3.5	A				
	Pulsed	I _{DP} *1	±14	±14	A				
Source current	Continuous	ls	1.6	-1.6	A				
(Body diode)	Pulsed	I _{SP} *1	14	-14	A				
Total power dissipation		Pd*2	2.0		W / TOTAL				
Channel temperature		Tch	150		°C				
Storage temperature		Tstg	-55 to +150		°C				

∗1 Pw≤10μs, Duty cycle≤1%

*2 Mounted on a ceramic board.

Transistors

N-ch

•Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	lgss	-	-	±10	μA	Vgs=±20V, Vds=0V
Drain-source breakdown voltage	V(BR) DSS	30	-	_	V	I _D = 1mA, V _{GS} =0V
Zero gate voltage drain current	IDSS	-	-	1	μΑ	V _{DS} = 30V, V _{GS} =0V
Gate threshold voltage	VGS (th)	1.0	-	2.5	V	V _{DS} = 10V, I _D = 1mA
		-	59	83	mΩ	I _D = 3.5A, V _{GS} = 10V
Static drain-source on-state resistance	$R_{DS}(on)^*$	-	93	130	mΩ	I _D = 3.5A, V _{GS} = 4.5V
resistance		-	107	150	mΩ	I _D = 3.5A, V _{GS} = 4V
Forward transfer admittance	Y _{fs} *	2.0	-	-	S	V _{DS} = 10V, I _D = 3.5A
Input capacitance	Ciss	-	140	_	pF	V _{DS} = 10V
Output capacitance	Coss	-	45	-	pF	V _{GS} =0V
Reverse transfer capacitance	Crss	-	30	-	pF	f=1MHz
Turn-on delay time	td (on) *	-	6	-	ns	Vdd≒ 15V
Rise time	tr *	-	6	-	ns	ID= 1.75A
Turn-off delay time	td (off) *	-	17	-	ns	Vgs= 10V RL= 8.57Ω
Fall time	t _f *	-	4	-	ns	$R_{G}=10\Omega$
Total gate charge	Qg *	-	2.5	3.5	nC	V _{DD} ≒15V, V _{GS} =5V
Gate-source charge	Q _{gs} *	-	0.8	_	nC	ID= 3.5A
Gate-drain charge	Q _{gd} *	_	0.8	-	nC	R _L = 4.29Ω, R _G = 10Ω

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd*	-	-	1.2	V	I _S = 6.4A, V _{GS} =0V
- Delevel						

*Pulsed

Transistors

P-ch

•Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	lgss	-	-	±10	μA	Vgs= ±20V, Vds=0V
Drain-source breakdown voltage	V(BR) DSS	-30	-	-	V	I _D = -1mA, V _{GS} =0V
Zero gate voltage drain current	IDSS	-	-	-1	μΑ	V_{DS} = -30V, V_{GS} =0V
Gate threshold voltage	VGS (th)	-1.0	-	-2.5	V	$V_{DS} = -10V, I_{D} = -1mA$
		-	65	90	mΩ	I _D = -3.5A, V _{GS} = -10V
Static drain-source on-state resistance	$R_{DS}(on)^*$	-	100	140	mΩ	I _D = -1.75A, V _{GS} = -4.5V
resistance		-	120	165	mΩ	I _D = -1.75A, V _{GS} = -4V
Forward transfer admittance	Y _{fs} *	1.8	-	_	S	V_{DS} = -10V, I_{D} = -1.75A
Input capacitance	Ciss	-	490	_	pF	V _{DS} = -10V
Output capacitance	Coss	-	110	-	pF	V _{GS} = 0V
Reverse transfer capacitance	Crss	-	75	-	pF	f=1MHz
Turn-on delay time	td (on) *	-	10	-	ns	Vdd≒-15V
Rise time	tr *	-	15	_	ns	$I_{D} = -1.75A$
Turn-off delay time	t _{d (off)} *	-	35	-	ns	Vgs= –10V RL= 8.57Ω
Fall time	t _f *	_	10	_	ns	$R_{G}=10\Omega$
Total gate charge	Qg *	-	5.5	7.7	nC	V _{DD} ≒−15V, V _{GS} =−5V
Gate-source charge	Q _{gs} *	-	1.5	-	nC	I _D = -3.5A
Gate-drain charge	Q _{gd} *	-	2.0	_	nC	R∟= 4.29Ω, R _G = 10Ω

●Body diode characteristics (Source-drain) (Ta=25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	Vsd*	-	-	-1.2	V	I _S = -1.6A, V _{GS} =0V
Delevel						

*Pulsed

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Appendix1-Rev2.0

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